

**Q. 1 – Q. 25 carry one mark each.**

Q.1 Consider a system of linear equations:

$$\begin{aligned}x - 2y + 3z &= -1, \\x - 3y + 4z &= 1, \text{ and} \\-2x + 4y - 6z &= k.\end{aligned}$$

The value of  $k$  for which the system has infinitely many solutions is \_\_\_\_\_.

Q.2 A function  $f(x) = 1 - x^2 + x^3$  is defined in the closed interval  $[-1, 1]$ . The value of  $x$ , in the open interval  $(-1, 1)$  for which the mean value theorem is satisfied, is

- (A)  $-1/2$                       (B)  $-1/3$                       (C)  $1/3$                       (D)  $1/2$

Q.3 Suppose  $A$  and  $B$  are two independent events with probabilities  $P(A) \neq 0$  and  $P(B) \neq 0$ . Let  $\bar{A}$  and  $\bar{B}$  be their complements. Which one of the following statements is FALSE?

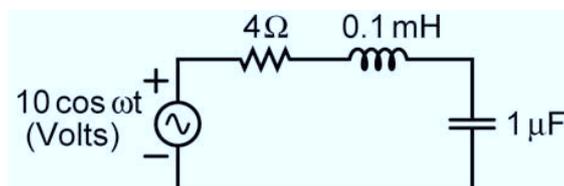
- (A)  $P(A \cap B) = P(A)P(B)$                       (B)  $P(A|B) = P(A)$   
 (C)  $P(A \cup B) = P(A) + P(B)$                       (D)  $P(\bar{A} \cap \bar{B}) = P(\bar{A})P(\bar{B})$

Q.4 Let  $z = x + iy$  be a complex variable. Consider that contour integration is performed along the unit circle in anticlockwise direction. Which one of the following statements is **NOT TRUE**?

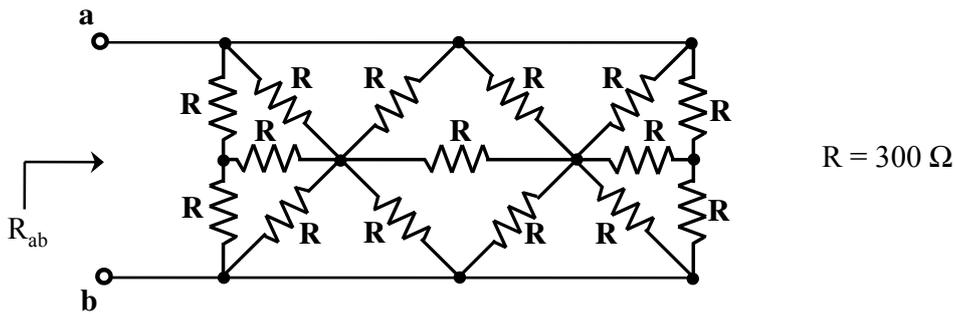
- (A) The residue of  $\frac{z}{z^2 - 1}$  at  $z = 1$  is  $1/2$   
 (B)  $\oint_C z^2 dz = 0$   
 (C)  $\frac{1}{2\pi i} \oint_C \frac{1}{z} dz = 1$   
 (D)  $\bar{z}$  (complex conjugate of  $z$ ) is an analytical function

Q.5 The value of  $p$  such that the vector  $\begin{bmatrix} 1 \\ 2 \\ 3 \end{bmatrix}$  is an eigenvector of the matrix  $\begin{bmatrix} 4 & 1 & 2 \\ p & 2 & 1 \\ 14 & -4 & 10 \end{bmatrix}$  is \_\_\_\_\_.

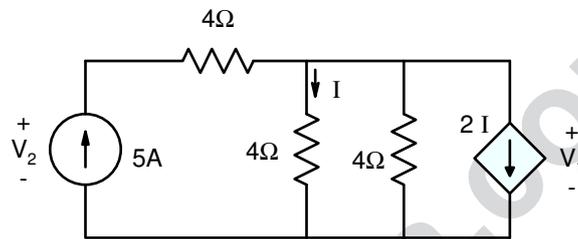
Q.6 In the circuit shown, at resonance, the amplitude of the sinusoidal voltage (in Volts) across the capacitor is \_\_\_\_\_.



Q.7 In the network shown in the figure, all resistors are identical with  $R = 300 \Omega$ . The resistance  $R_{ab}$  (in  $\Omega$ ) of the network is \_\_\_\_\_.



Q.8 In the given circuit, the values of  $V_1$  and  $V_2$  respectively are



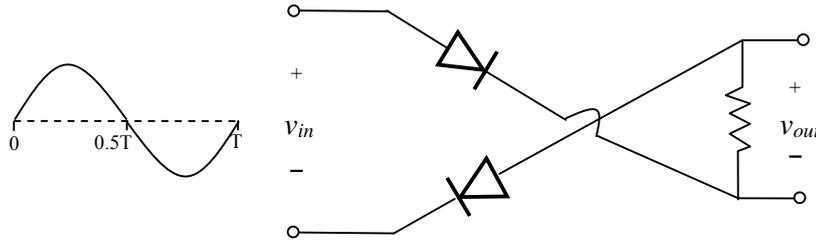
- (A) 5 V, 25 V      (B) 10 V, 30 V      (C) 15 V, 35 V      (D) 0 V, 20 V

Q.9 A region of negative differential resistance is observed in the current voltage characteristics of a silicon PN junction if

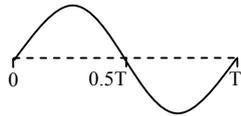
- (A) both the P-region and the N-region are heavily doped
- (B) the N-region is heavily doped compared to the P-region
- (C) the P-region is heavily doped compared to the N-region
- (D) an intrinsic silicon region is inserted between the P-region and the N-region

Q.10 A silicon sample is uniformly doped with donor type impurities with a concentration of  $10^{16} / \text{cm}^3$ . The electron and hole mobilities in the sample are  $1200 \text{ cm}^2/\text{V-s}$  and  $400 \text{ cm}^2/\text{V-s}$  respectively. Assume complete ionization of impurities. The charge of an electron is  $1.6 \times 10^{-19} \text{ C}$ . The resistivity of the sample (in  $\Omega\text{-cm}$ ) is \_\_\_\_\_.

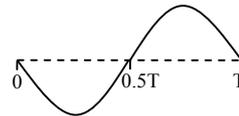
Q.11 For the circuit with ideal diodes shown in the figure, the shape of the output ( $v_{out}$ ) for the given sine wave input ( $v_{in}$ ) will be



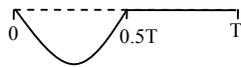
(A)



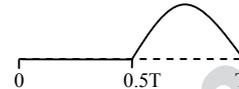
(B)



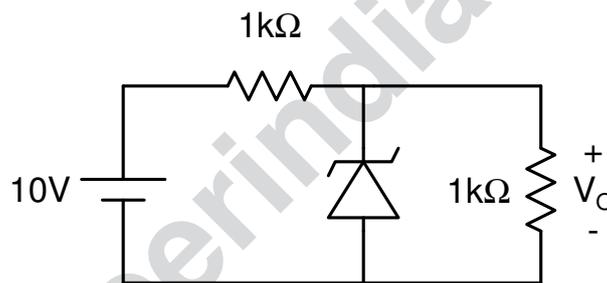
(C)



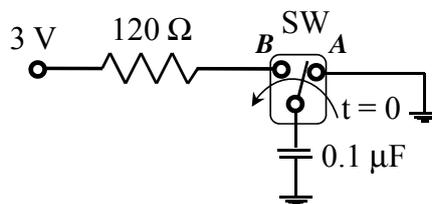
(D)



Q.12 In the circuit shown below, the Zener diode is ideal and the Zener voltage is 6 V. The output voltage  $V_o$  (in volts) is \_\_\_\_\_.



Q.13 In the circuit shown, the switch SW is thrown from position A to position B at time  $t = 0$ . The energy (in  $\mu\text{J}$ ) taken from the 3 V source to charge the  $0.1 \mu\text{F}$  capacitor from 0 V to 3 V is



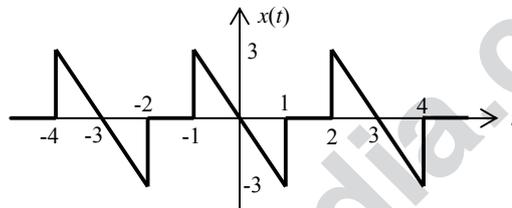
(A) 0.3

(B) 0.45

(C) 0.9

(D) 3

- Q.14 In an 8085 microprocessor, the shift registers which store the result of an addition and the overflow bit are, respectively
- (A) B and F  
 (B) A and F  
 (C) H and F  
 (D) A and C
- Q.15 A 16 Kb (=16,384 bit) memory array is designed as a square with an aspect ratio of one (number of rows is equal to the number of columns). The minimum number of address lines needed for the row decoder is \_\_\_\_\_.
- Q.16 Consider a four bit D to A converter. The analog value corresponding to digital signals of values 0000 and 0001 are 0 V and 0.0625 V respectively. The analog value (in Volts) corresponding to the digital signal 1111 is \_\_\_\_\_.
- Q.17 The result of the convolution  $x(-t) * \delta(-t - t_0)$  is
- (A)  $x(t + t_0)$       (B)  $x(t - t_0)$       (C)  $x(-t + t_0)$       (D)  $x(-t - t_0)$
- Q.18 The waveform of a periodic signal  $x(t)$  is shown in the figure.



A signal  $g(t)$  is defined by  $g(t) = x\left(\frac{t-1}{2}\right)$ . The average power of  $g(t)$  is \_\_\_\_\_.

- Q.19 Negative feedback in a closed-loop control system **DOES NOT**
- (A) reduce the overall gain      (B) reduce bandwidth  
 (C) improve disturbance rejection      (D) reduce sensitivity to parameter variation
- Q.20 A unity negative feedback system has the open-loop transfer function  $G(s) = \frac{K}{s(s+1)(s+3)}$ . The value of the gain  $K$  ( $>0$ ) at which the root locus crosses the imaginary axis is \_\_\_\_\_.
- Q.21 The polar plot of the transfer function  $G(s) = \frac{10(s+1)}{s+10}$  for  $0 \leq \omega < \infty$  will be in the
- (A) first quadrant  
 (B) second quadrant  
 (C) third quadrant  
 (D) fourth quadrant

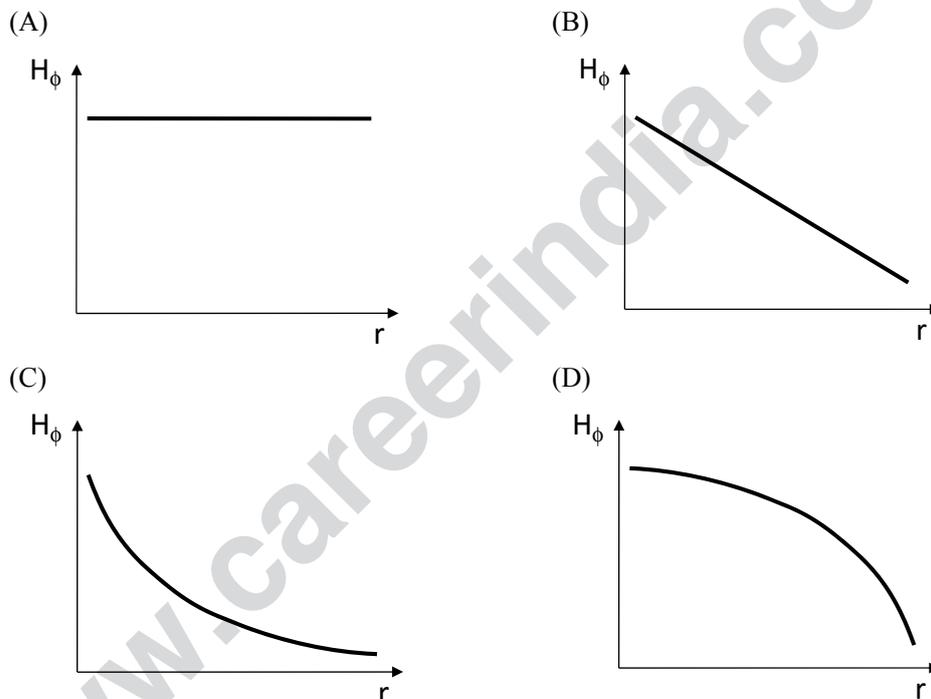
Q.22 A sinusoidal signal of 2 kHz frequency is applied to a delta modulator. The sampling rate and step-size  $\Delta$  of the delta modulator are 20,000 samples per second and 0.1 V, respectively. To prevent slope overload, the maximum amplitude of the sinusoidal signal (in Volts) is

- (A)  $\frac{1}{2\pi}$  (B)  $\frac{1}{\pi}$   
 (C)  $\frac{2}{\pi}$  (D)  $\pi$

Q.23 Consider the signal  $s(t) = m(t) \cos(2\pi f_c t) + \hat{m}(t) \sin(2\pi f_c t)$  where  $\hat{m}(t)$  denotes the Hilbert transform of  $m(t)$  and the bandwidth of  $m(t)$  is very small compared to  $f_c$ . The signal  $s(t)$  is a

- (A) high-pass signal  
 (B) low-pass signal  
 (C) band-pass signal  
 (D) double sideband suppressed carrier signal

Q.24 Consider a straight, infinitely long, current carrying conductor lying on the  $z$ -axis. Which one of the following plots (in linear scale) qualitatively represents the dependence of  $H_\phi$  on  $r$ , where  $H_\phi$  is the magnitude of the azimuthal component of magnetic field outside the conductor and  $r$  is the radial distance from the conductor?



Q.25 The electric field component of a plane wave traveling in a lossless dielectric medium is given by

$$\vec{E}(z, t) = \hat{a}_y 2 \cos\left(10^8 t - \frac{z}{\sqrt{2}}\right) \text{ V/m. The wavelength (in m) for the wave is _____.$$

**Q. 26 – Q. 55 carry two marks each.**

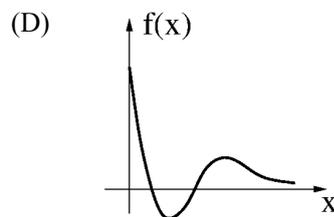
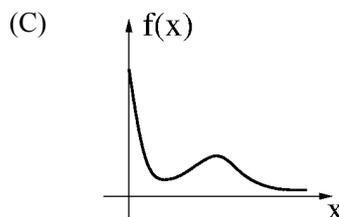
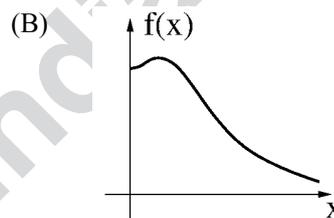
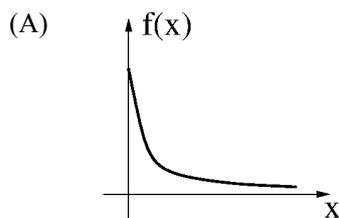
Q.26 The solution of the differential equation  $\frac{d^2y}{dt^2} + 2\frac{dy}{dt} + y = 0$  with  $y(0) = y'(0) = 1$  is

- (A)  $(2-t)e^t$  (B)  $(1+2t)e^{-t}$   
 (C)  $(2+t)e^{-t}$  (D)  $(1-2t)e^t$

Q.27 A vector  $\vec{P}$  is given by  $\vec{P} = x^3y \vec{a}_x - x^2y^2 \vec{a}_y - x^2yz \vec{a}_z$ . Which one of the following statements is **TRUE**?

- (A)  $\vec{P}$  is solenoidal, but not irrotational  
 (B)  $\vec{P}$  is irrotational, but not solenoidal  
 (C)  $\vec{P}$  is neither solenoidal nor irrotational  
 (D)  $\vec{P}$  is both solenoidal and irrotational

Q.28 Which one of the following graphs describes the function  $f(x) = e^{-x}(x^2 + x + 1)$ ?

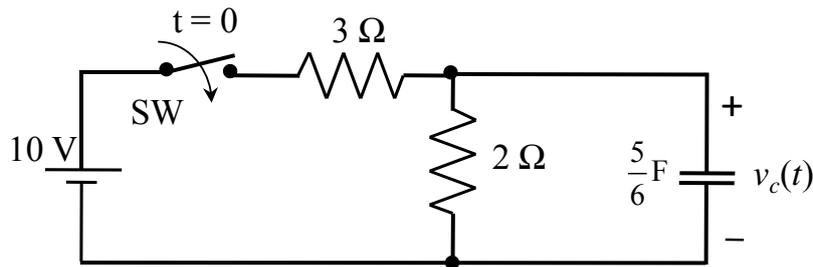


Q.29 The maximum area (in square units) of a rectangle whose vertices lie on the ellipse  $x^2 + 4y^2 = 1$  is \_\_\_\_\_.

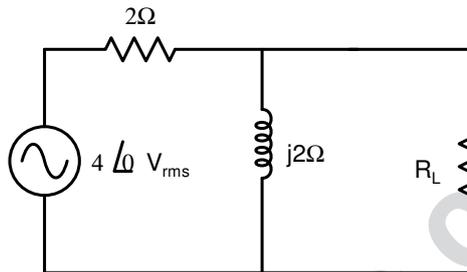
Q.30 The damping ratio of a series *RLC* circuit can be expressed as

- (A)  $\frac{R^2C}{2L}$  (B)  $\frac{2L}{R^2C}$  (C)  $\frac{R}{2}\sqrt{\frac{C}{L}}$  (D)  $\frac{2}{R}\sqrt{\frac{L}{C}}$

- Q.31 In the circuit shown, switch SW is closed at  $t = 0$ . Assuming zero initial conditions, the value of  $v_c(t)$  (in Volts) at  $t = 1$  sec is \_\_\_\_\_.

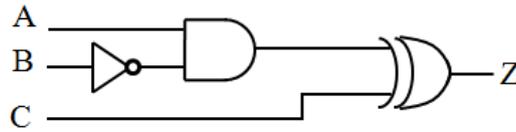


- Q.32 In the given circuit, the maximum power (in Watts) that can be transferred to the load  $R_L$  is \_\_\_\_\_.



- Q.33 The built-in potential of an abrupt p-n junction is 0.75 V. If its junction capacitance ( $C_j$ ) at a reverse bias ( $V_R$ ) of 1.25 V is 5 pF, the value of  $C_j$  (in pF) when  $V_R = 7.25$  V is \_\_\_\_\_.
- Q.34 A MOSFET in saturation has a drain current of 1 mA for  $V_{DS} = 0.5$  V. If the channel length modulation coefficient is  $0.05 \text{ V}^{-1}$ , the output resistance (in  $\text{k}\Omega$ ) of the MOSFET is \_\_\_\_\_.
- Q.35 For a silicon diode with long P and N regions, the acceptor and donor impurity concentrations are  $1 \times 10^{17} \text{ cm}^{-3}$  and  $1 \times 10^{15} \text{ cm}^{-3}$ , respectively. The lifetimes of electrons in P region and holes in N region are both 100  $\mu\text{s}$ . The electron and hole diffusion coefficients are 49  $\text{cm}^2/\text{s}$  and 36  $\text{cm}^2/\text{s}$ , respectively. Assume  $kT/q = 26$  mV, the intrinsic carrier concentration is  $1 \times 10^{10} \text{ cm}^{-3}$ , and  $q = 1.6 \times 10^{-19}$  C. When a forward voltage of 208 mV is applied across the diode, the hole current density (in  $\text{nA}/\text{cm}^2$ ) injected from P region to N region is \_\_\_\_\_.
- Q.36 The Boolean expression  $F(X,Y,Z) = \bar{X}Y\bar{Z} + X\bar{Y}\bar{Z} + XY\bar{Z} + XYZ$  converted into the canonical product of sum (POS) form is
- (A)  $(X+Y+Z)(X+Y+\bar{Z})(X+\bar{Y}+\bar{Z})(\bar{X}+Y+\bar{Z})$     (B)  $(X+\bar{Y}+Z)(\bar{X}+Y+\bar{Z})(\bar{X}+\bar{Y}+Z)(\bar{X}+\bar{Y}+\bar{Z})$   
 (C)  $(X+Y+Z)(\bar{X}+Y+\bar{Z})(X+\bar{Y}+Z)(\bar{X}+\bar{Y}+\bar{Z})$     (D)  $(X+\bar{Y}+\bar{Z})(\bar{X}+Y+Z)(\bar{X}+\bar{Y}+Z)(X+Y+Z)$

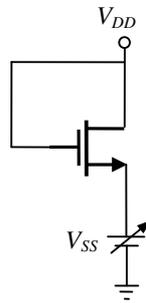
Q.37 All the logic gates shown in the figure have a propagation delay of 20 ns. Let  $A = C = 0$  and  $B = 1$  until time  $t = 0$ . At  $t = 0$ , all the inputs flip (i.e.,  $A = C = 1$  and  $B = 0$ ) and remain in that state. For  $t > 0$ , output  $Z = 1$  for a duration (in ns) of \_\_\_\_\_.



Q.38 A 3-input majority gate is defined by the logic function  $M(a,b,c) = ab + bc + ca$ . Which one of the following gates is represented by the function  $M(M(a,b,c), M(a,b,\bar{c}), c)$  ?

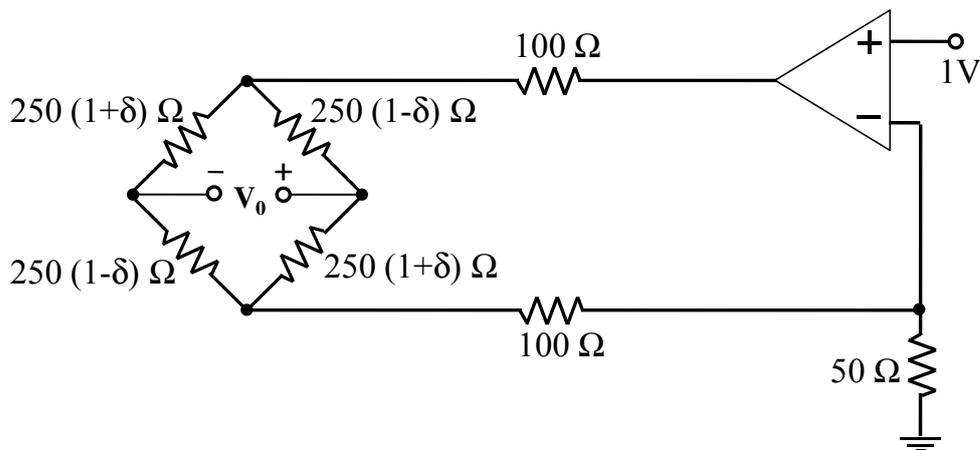
- (A) 3-input NAND gate
- (B) 3-input XOR gate
- (C) 3-input NOR gate
- (D) 3-input XNOR gate

Q.39 For the NMOSFET in the circuit shown, the threshold voltage is  $V_{th}$ , where  $V_{th} > 0$ . The source voltage  $V_{SS}$  is varied from 0 to  $V_{DD}$ . Neglecting the channel length modulation, the drain current  $I_D$  as a function of  $V_{SS}$  is represented by

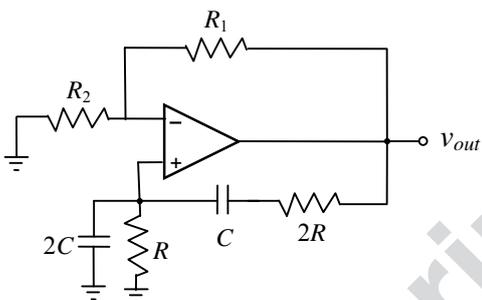


- (A)
- (B)
- (C)
- (D)

Q.40 In the circuit shown, assume that the opamp is ideal. The bridge output voltage  $V_0$  (in mV) for  $\delta = 0.05$  is \_\_\_\_\_.

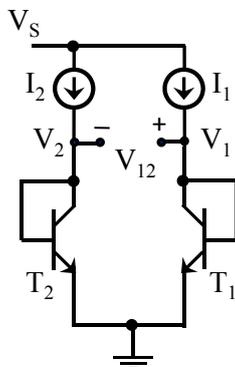


Q.41 The circuit shown in the figure has an ideal opamp. The oscillation frequency and the condition to sustain the oscillations, respectively, are



- (A)  $\frac{1}{CR}$  and  $R_1 = R_2$
- (B)  $\frac{1}{CR}$  and  $R_1 = 4R_2$
- (C)  $\frac{1}{2CR}$  and  $R_1 = R_2$
- (D)  $\frac{1}{2CR}$  and  $R_1 = 4R_2$

Q.42 In the circuit shown,  $I_1 = 80$  mA and  $I_2 = 4$  mA. Transistors  $T_1$  and  $T_2$  are identical. Assume that the thermal voltage  $V_T$  is 26 mV at 27 °C. At 50 °C, the value of the voltage  $V_{12} = V_1 - V_2$  (in mV) is \_\_\_\_\_.



Q.43 Two sequences  $[a, b, c]$  and  $[A, B, C]$  are related as,

$$\begin{bmatrix} A \\ B \\ C \end{bmatrix} = \begin{bmatrix} 1 & 1 & 1 \\ 1 & W_3^{-1} & W_3^{-2} \\ 1 & W_3^{-2} & W_3^{-4} \end{bmatrix} \begin{bmatrix} a \\ b \\ c \end{bmatrix} \text{ where } W_3 = e^{j\frac{2\pi}{3}}.$$

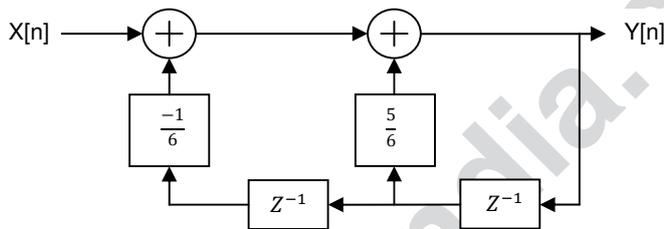
If another sequence  $[p, q, r]$  is derived as,

$$\begin{bmatrix} p \\ q \\ r \end{bmatrix} = \begin{bmatrix} 1 & 1 & 1 \\ 1 & W_3^1 & W_3^2 \\ 1 & W_3^2 & W_3^4 \end{bmatrix} \begin{bmatrix} A/3 \\ B/3 \\ C/3 \end{bmatrix},$$

then the relationship between the sequences  $[p, q, r]$  and  $[a, b, c]$  is

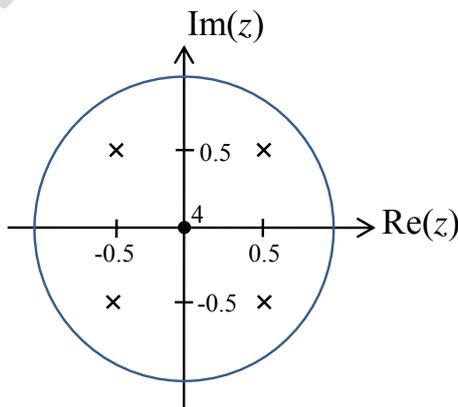
- (A)  $[p, q, r] = [b, a, c]$
- (B)  $[p, q, r] = [b, c, a]$
- (C)  $[p, q, r] = [c, a, b]$
- (D)  $[p, q, r] = [c, b, a]$

Q.44 For the discrete-time system shown in the figure, the poles of the system transfer function are located at



- (A) 2, 3
- (B)  $\frac{1}{2}, 3$
- (C)  $\frac{1}{2}, \frac{1}{3}$
- (D)  $2, \frac{1}{3}$

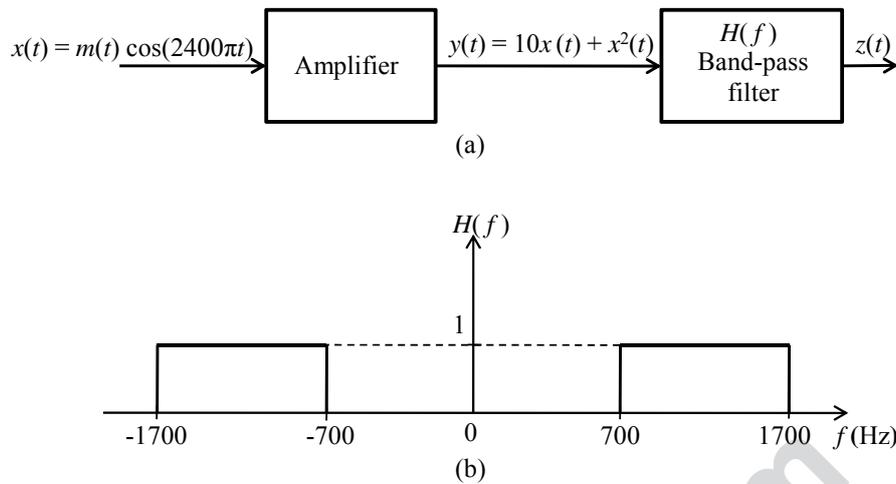
Q.45 The pole-zero diagram of a causal and stable discrete-time system is shown in the figure. The zero at the origin has multiplicity 4. The impulse response of the system is  $h[n]$ . If  $h[0] = 1$ , we can conclude



- (A)  $h[n]$  is real for all  $n$
- (B)  $h[n]$  is purely imaginary for all  $n$
- (C)  $h[n]$  is real for only even  $n$
- (D)  $h[n]$  is purely imaginary for only odd  $n$



- Q.51 In the system shown in Figure (a),  $m(t)$  is a low-pass signal with bandwidth  $W$  Hz. The frequency response of the band-pass filter  $H(f)$  is shown in Figure (b). If it is desired that the output signal  $z(t) = 10x(t)$ , the maximum value of  $W$  (in Hz) should be strictly less than \_\_\_\_\_.



- Q.52 A source emits bit 0 with probability  $\frac{1}{3}$  and bit 1 with probability  $\frac{2}{3}$ . The emitted bits are communicated to the receiver. The receiver decides for either 0 or 1 based on the received value  $R$ . It is given that the conditional density functions of  $R$  are as

$$f_{R|0}(r) = \begin{cases} \frac{1}{4}, & -3 \leq r \leq 1, \\ 0, & \text{otherwise,} \end{cases} \quad \text{and} \quad f_{R|1}(r) = \begin{cases} \frac{1}{6}, & -1 \leq r \leq 5, \\ 0, & \text{otherwise.} \end{cases}$$

The minimum decision error probability is

- (A) 0                      (B) 1/12                      (C) 1/9                      (D) 1/6
- Q.53 The longitudinal component of the magnetic field inside an air-filled rectangular waveguide made of a perfect electric conductor is given by the following expression

$$H_z(x, y, z, t) = 0.1 \cos(25\pi x) \cos(30.3\pi y) \cos(12\pi \times 10^9 t - \beta z) \quad (\text{A/m})$$

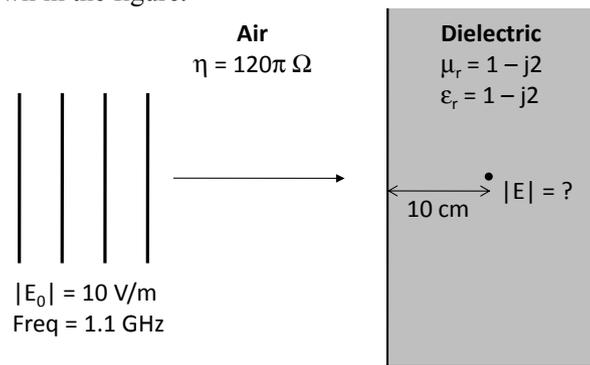
The cross-sectional dimensions of the waveguide are given as  $a = 0.08$  m and  $b = 0.033$  m. The mode of propagation inside the waveguide is

- (A)  $TM_{12}$                       (B)  $TM_{21}$   
 (C)  $TE_{21}$                       (D)  $TE_{12}$
- Q.54 The electric field intensity of a plane wave traveling in free space is given by the following expression

$$\mathbf{E}(x, t) = \mathbf{a}_y 24 \pi \cos(\omega t - k_0 x) \quad (\text{V/m})$$

In this field, consider a square area 10 cm x 10 cm on a plane  $x + y = 1$ . The total time-averaged power (in mW) passing through the square area is \_\_\_\_\_.

- Q.55 Consider a uniform plane wave with amplitude ( $E_0$ ) of 10 V/m and 1.1 GHz frequency travelling in air, and incident normally on a dielectric medium with complex relative permittivity ( $\epsilon_r$ ) and permeability ( $\mu_r$ ) as shown in the figure.



The magnitude of the transmitted electric field component (in V/m) after it has travelled a distance of 10 cm inside the dielectric region is \_\_\_\_\_.

**END OF THE QUESTION PAPER**